

Maximum Ratings at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	150	V
Forward current	I_F	100	mA
Total power dissipation	P_{tot}		mW
BAR64-02EL, $T_S \leq 135^\circ\text{C}$		250	
BAR64-02V, $T_S \leq 125^\circ\text{C}$		250	
BAR64-03W, $T_S \leq 25^\circ\text{C}$		250	
BAR64-04, -05, -06, $T_S \leq 65^\circ\text{C}$		250	
BAR64-04W, -05W, -06W, $T_S \leq 115^\circ\text{C}$		250	
Junction temperature	T_j	150	$^\circ\text{C}$
Operating temperature range	T_{op}	-55 ... 125	
Storage temperature	T_{stg}	-55 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R_{thJS}		
BAR64-02EL		≤ 60	
BAR64-02V, -04W, -05W, -06W		≤ 140	
BAR64-03W		≤ 370	
BAR64-04, -05, -06		≤ 340	

¹⁾For calculation of R_{thJA} please refer to Application Note AN077 (Thermal Resistance Calculation)

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

DC Characteristics

Breakdown voltage	$V_{(\text{BR})}$	150	-	-	V
$I_{(\text{BR})} = 5 \mu\text{A}$					
Forward voltage	V_F	-	-	1.1	
$I_F = 50 \text{ mA}$					

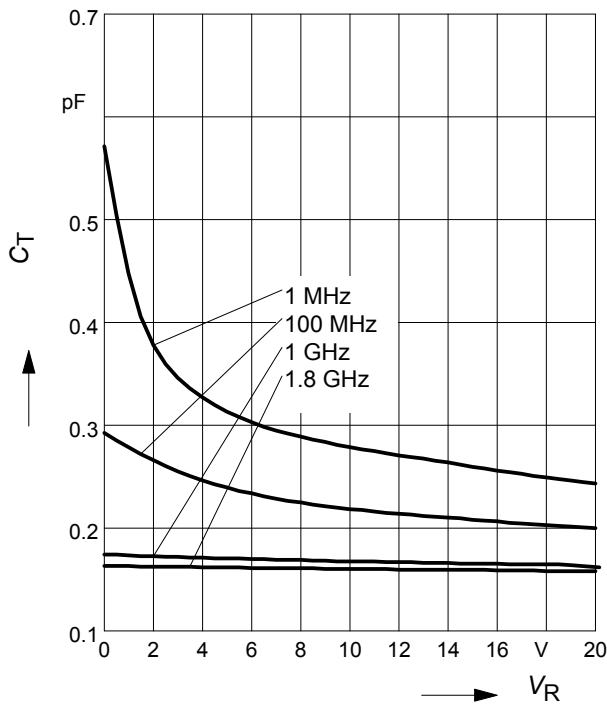
Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics					
Diode capacitance $V_R = 20\text{ V}$, $f = 1\text{ MHz}$ $V_R = 0\text{ V}$, $f = 100\text{ MHz}$ $V_R = 0\text{ V}$, $f = 1\ldots 1.8\text{ GHz}$, BAR64-02EL $V_R = 0\text{ V}$, $f = 1\ldots 1.8\text{ GHz}$, all other	C_T	- - - -	0.23 0.3 0.13 0.17	0.35 - - -	pF
Reverse parallel resistance $V_R = 0\text{ V}$, $f = 100\text{ MHz}$ $V_R = 0\text{ V}$, $f = 1\text{ GHz}$ $V_R = 0\text{ V}$, $f = 1.8\text{ GHz}$	R_P	- - -	10 4 3	- - -	kΩ
Forward resistance $I_F = 1\text{ mA}$, $f = 100\text{ MHz}$ $I_F = 10\text{ mA}$, $f = 100\text{ MHz}$ $I_F = 100\text{ mA}$, $f = 100\text{ MHz}$	r_f	- - -	12.5 2.1 0.85	20 2.8 1.35	Ω
Charge carrier life time $I_F = 10\text{ mA}$, $I_R = 6\text{ mA}$, measured at $I_R = 3\text{ mA}$, $R_L = 100\text{ Ω}$	τ_{rr}	-	1550	-	ns
I-region width	W_I	-	50	-	μm
Insertion loss ¹⁾ $I_F = 3\text{ mA}$, $f = 1.8\text{ GHz}$ $I_F = 5\text{ mA}$, $f = 1.8\text{ GHz}$ $I_F = 10\text{ mA}$, $f = 1.8\text{ GHz}$	I_L	- - -	0.32 0.23 0.16	- - -	dB
Isolation ¹⁾ $V_R = 0\text{ V}$, $f = 0.9\text{ GHz}$ $V_R = 0\text{ V}$, $f = 1.8\text{ GHz}$ $V_R = 0\text{ V}$, $f = 2.45\text{ GHz}$ $V_R = 0\text{ V}$, $f = 5.6\text{ GHz}$	I_{SO}	- - - -	22 17 14.5 8.5	- - - -	

¹⁾BAR64-02EL in series configuration, $Z = 50\text{ }\Omega$

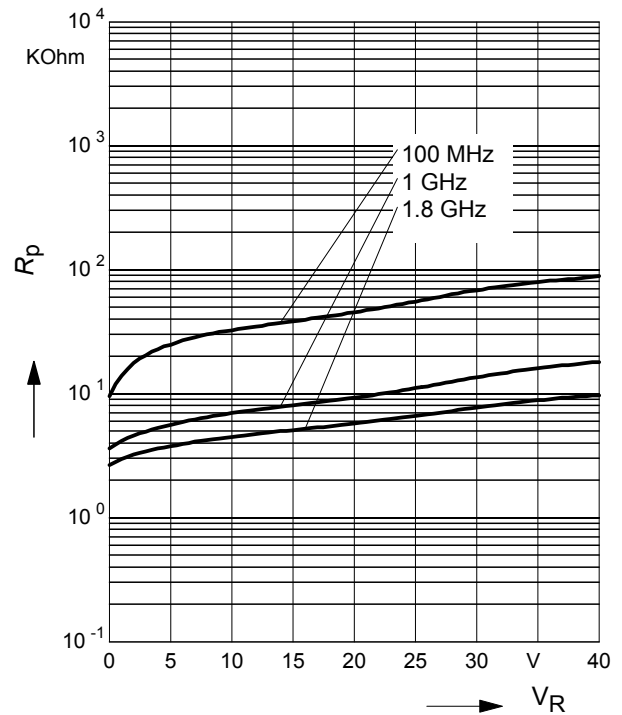
Diode capacitance $C_T = f(V_R)$

f = Parameter



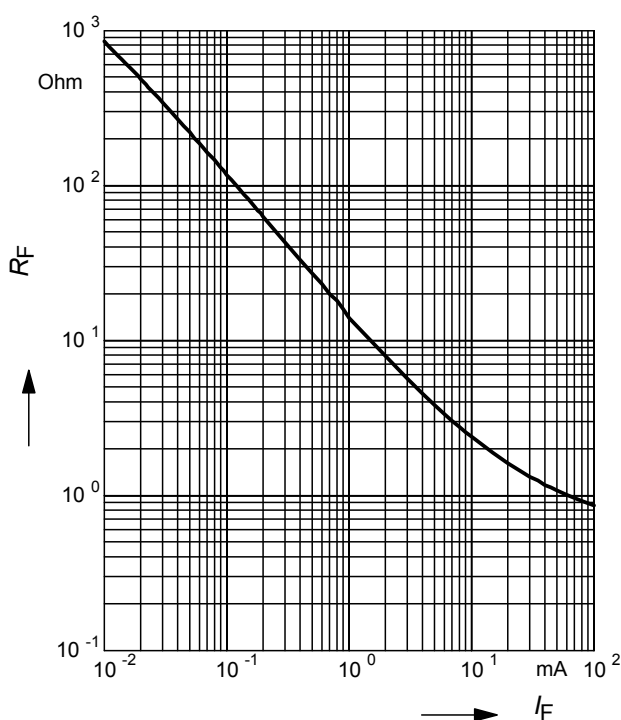
Reverse parallel resistance $R_P = f(V_R)$

f = Parameter



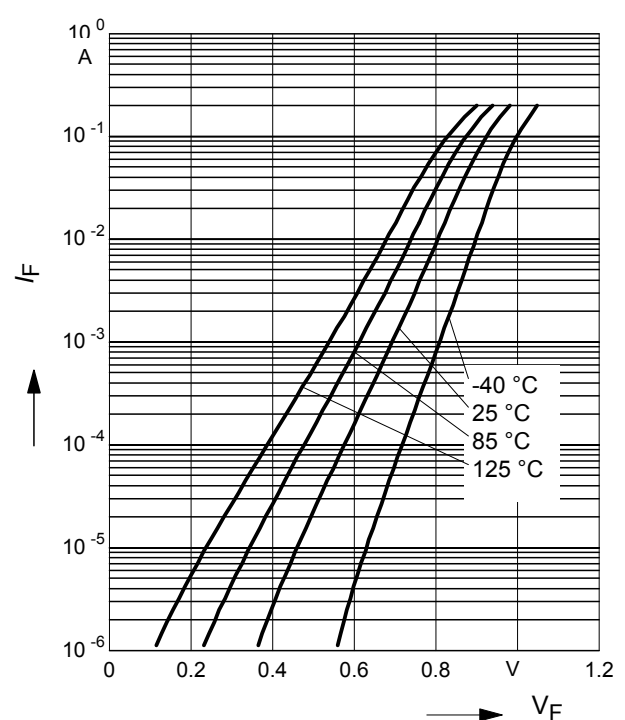
Forward resistance $r_f = f(I_F)$

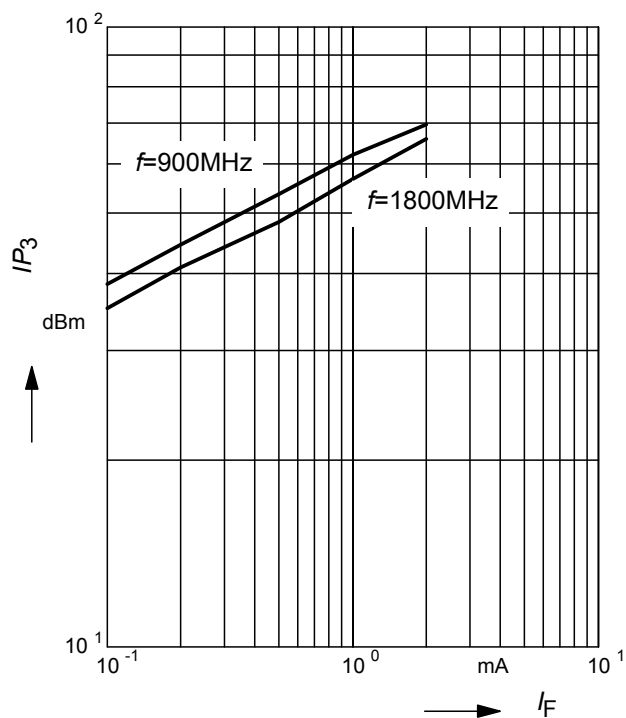
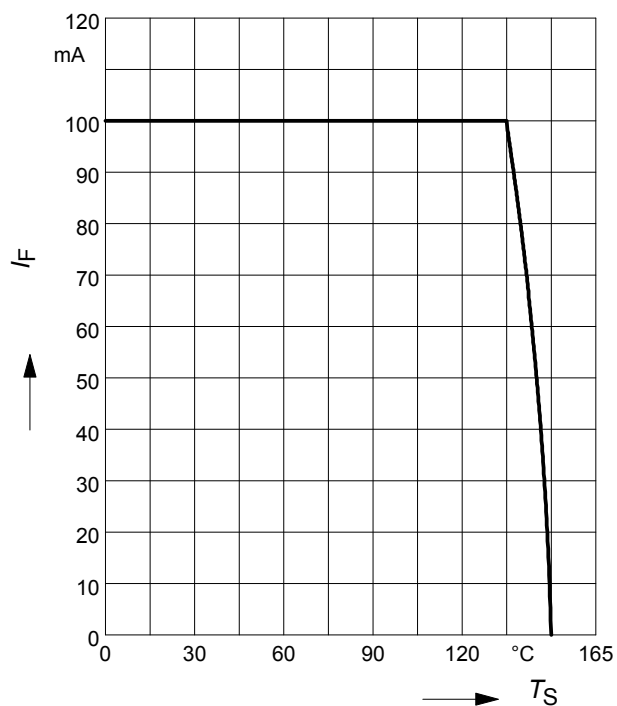
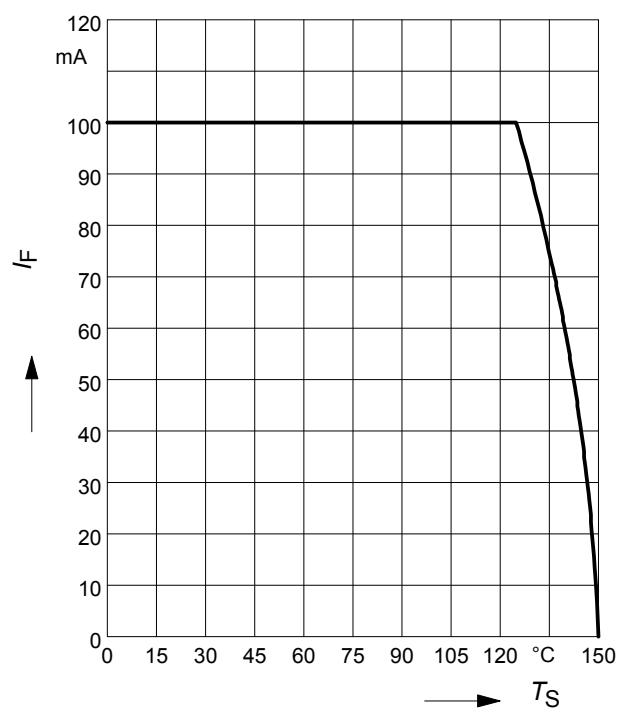
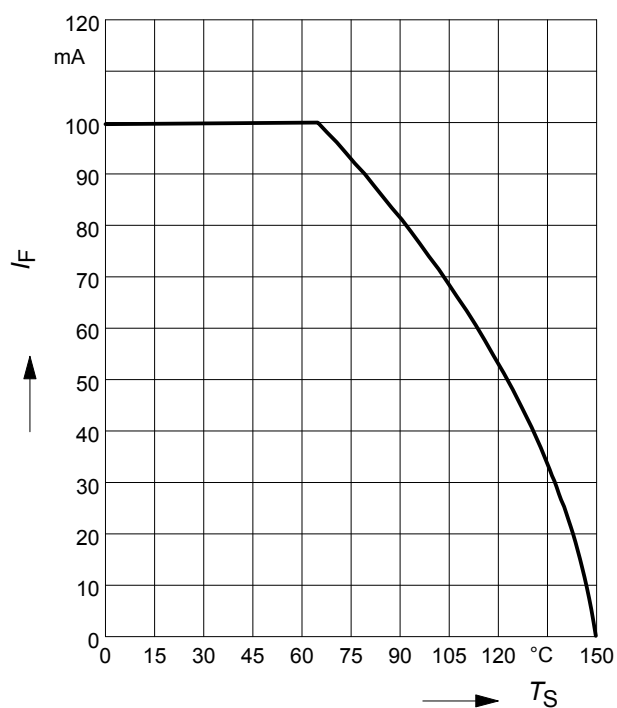
f = 100MHz



Forward current $I_F = f(V_F)$

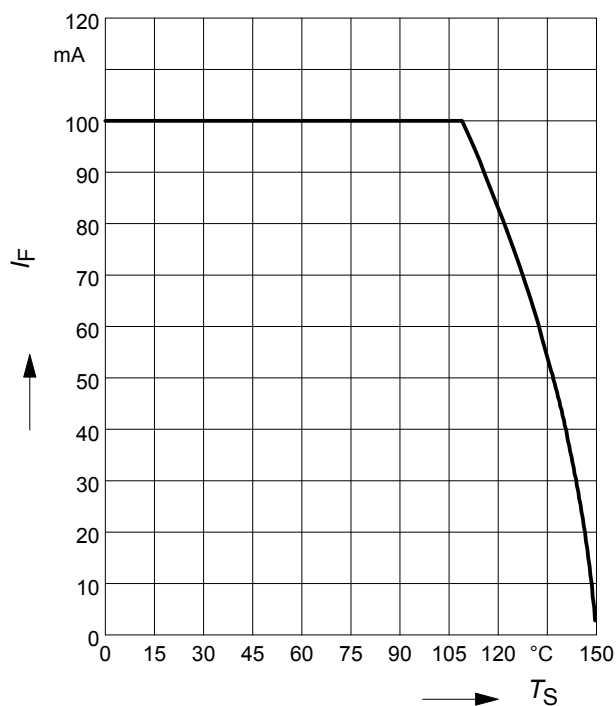
T_A = Parameter



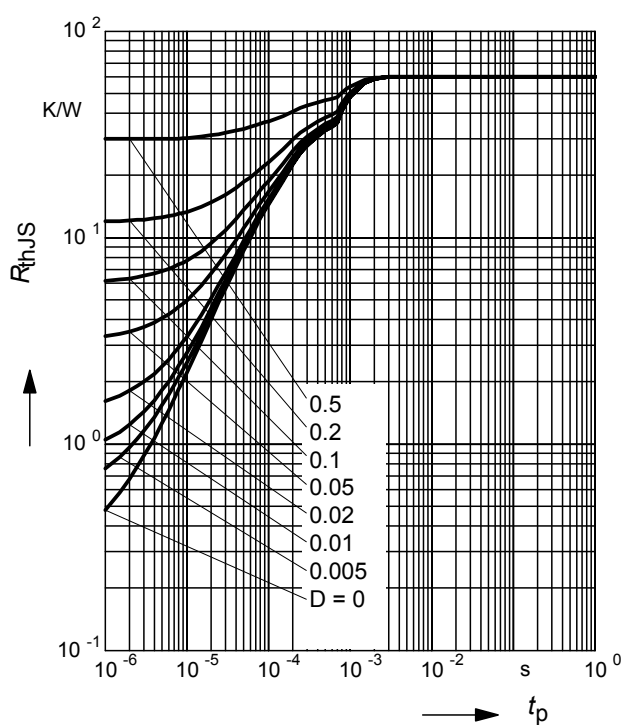
Intermodulation intercept point
 $IP_3 = f(I_F); f = \text{Parameter}$

Forward current $I_F = f(T_S)$
BAR64-02EL

Forward current $I_F = f(T_S)$
BAR64-02V

Forward current $I_F = f(T_S)$
BAR64-04, BAR64-05, BAR64-06


Forward current $I_F = f(T_S)$

BAR64-04W, BAR64-05W, BAR64-06W

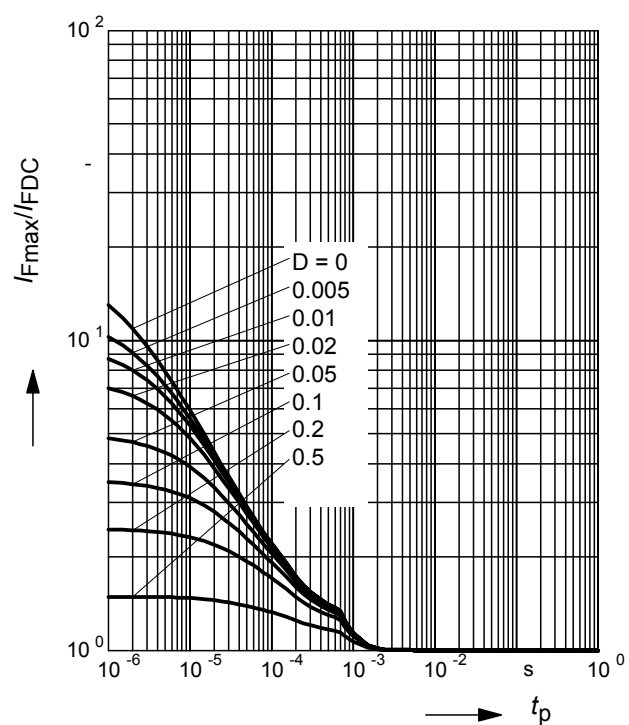

Permissible Puls Load $R_{thJS} = f(t_p)$

BAR64-02EL


Permissible Pulse Load

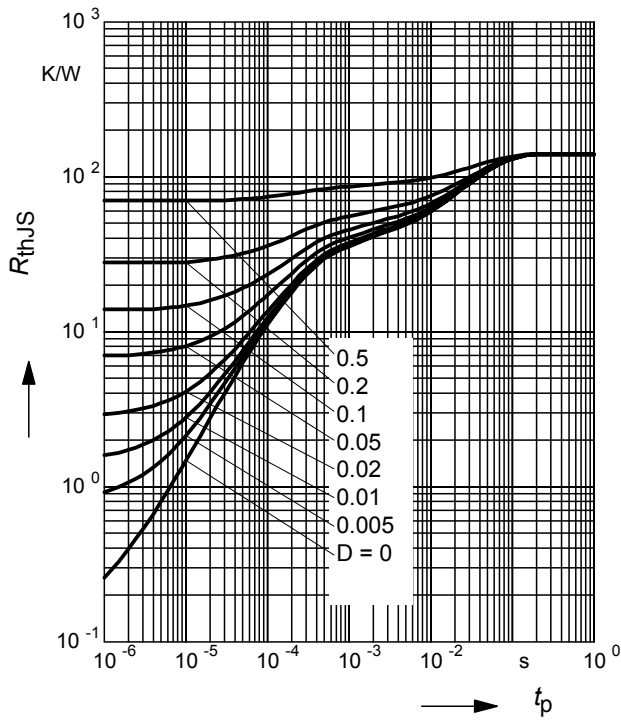
$$I_{Fmax}/I_{FDC} = f(t_p)$$

BAR64-02EL



Permissible Puls Load $R_{thJS} = f(t_p)$

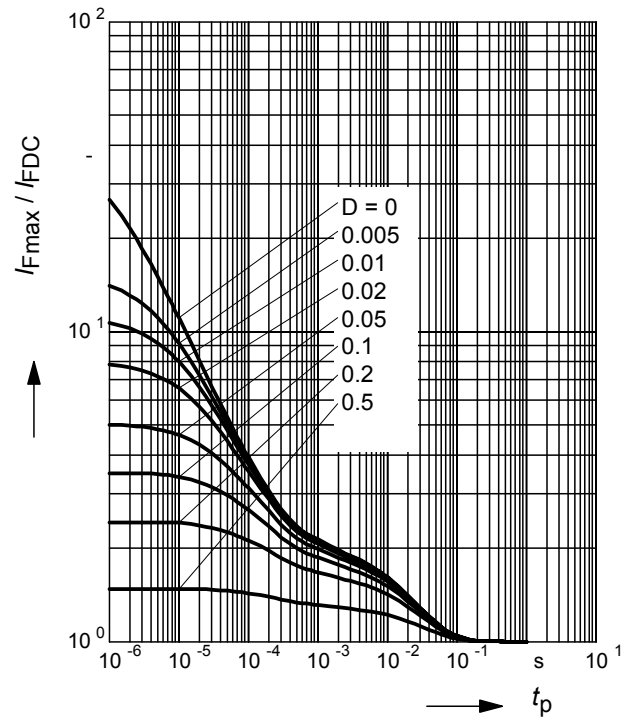
BAR64-02V



Permissible Pulse Load

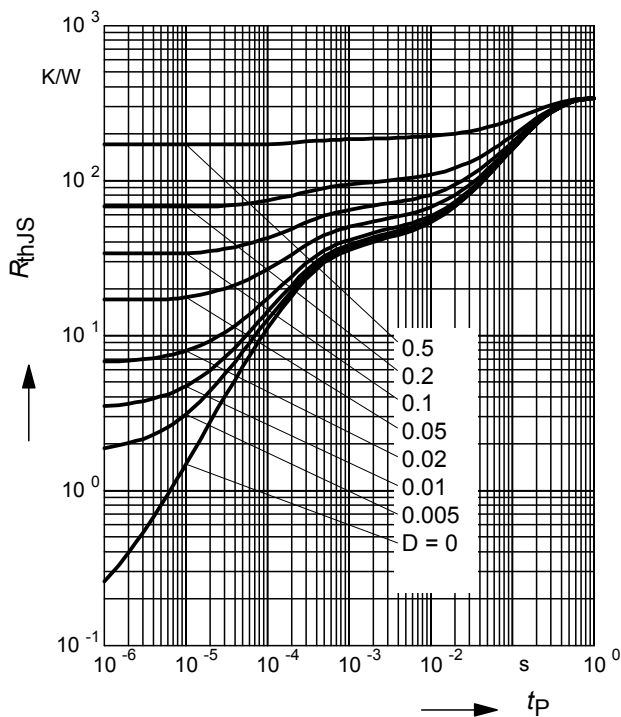
$$I_{Fmax} / I_{FDC} = f(t_p)$$

BAR64-02V



Permissible Puls Load $R_{thJS} = f(t_p)$

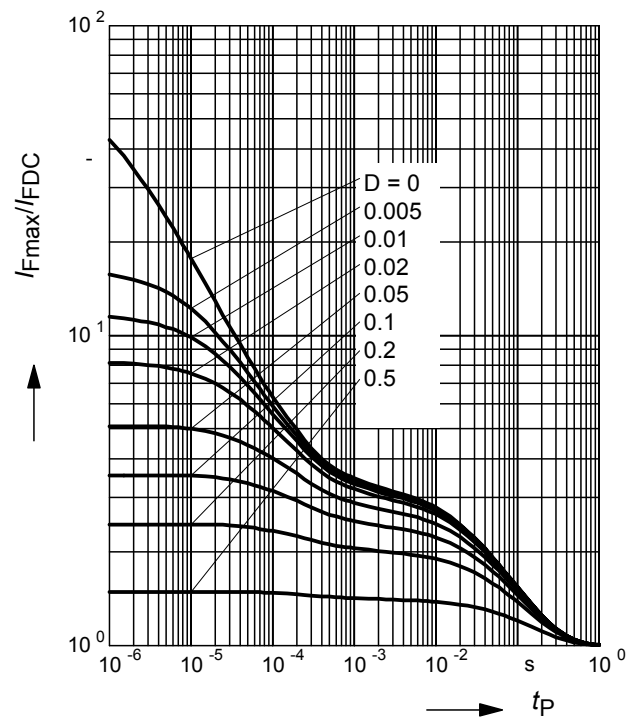
BAR64-04, BAR64-05, BAR64-06



Permissible Pulse Load

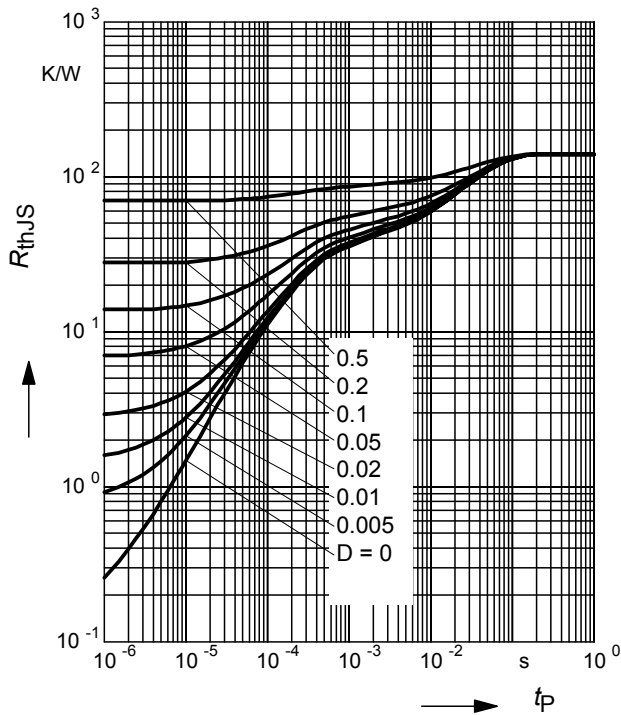
$$I_{Fmax} / I_{FDC} = f(t_p)$$

BAR64-04, BAR64-05, BAR64-06



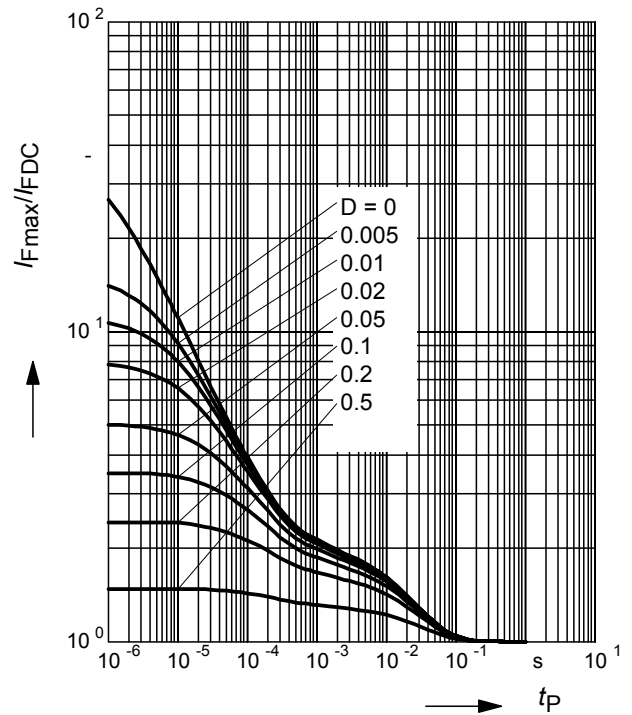
Permissible Puls Load $R_{thJS} = f(t_p)$

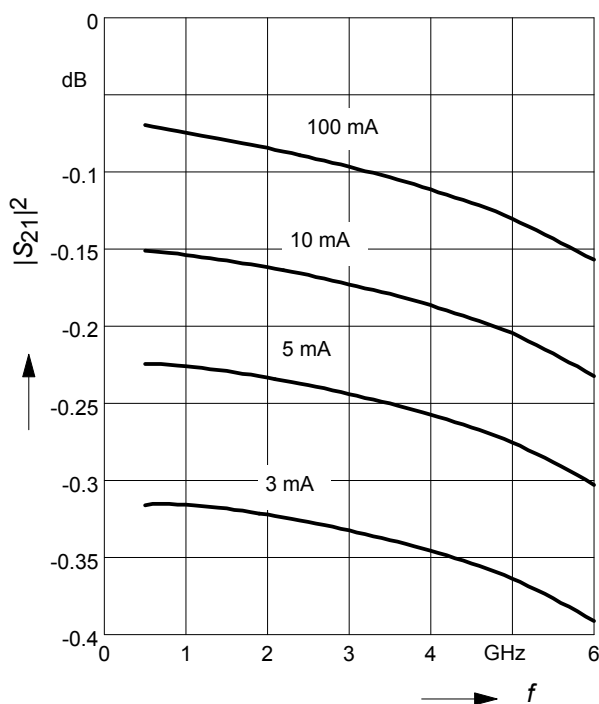
BAR64-04W, BAR64-05W, BAR64-06W

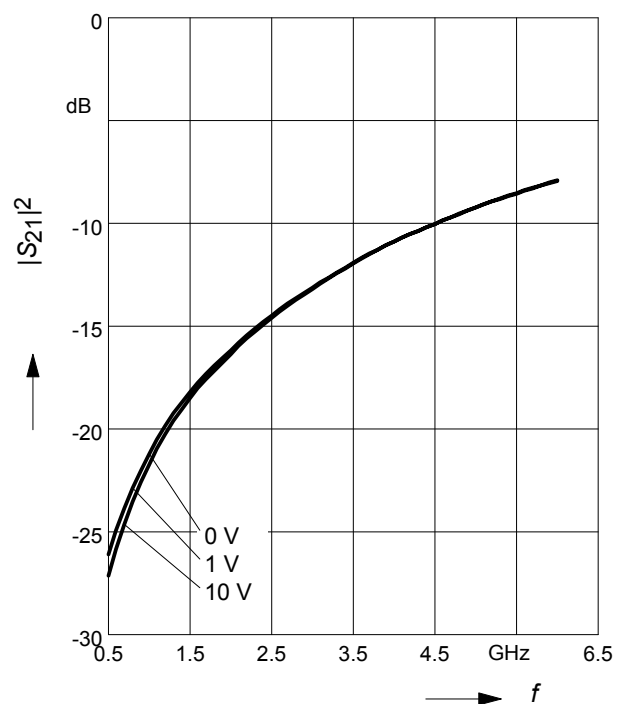

Permissible Pulse Load

$$I_{Fmax}/I_{FDC} = f(t_p)$$

BAR64-04W, BAR64-05W, BAR64-06W


Insertion loss $I_L = -|S_{21}|^2 = f(f)$
 I_F = Parameter

 BAR64-02EL in series configuration, $Z = 50\Omega$

Isolation $I_{SO} = -|S_{21}|^2 = f(f)$
 V_R = Parameter

 BAR64-02EL in series configuration, $Z = 50\Omega$


Package Outline



Foot Print

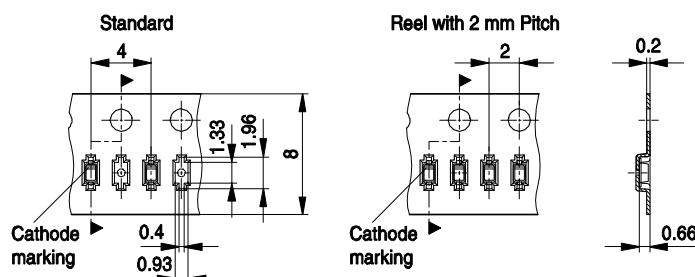


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel
 Reel ø180 mm = 8.000 Pieces/Reel (2 mm Pitch)
 Reel ø330 mm = 10.000 Pieces/Reel



Date Code marking for discrete packages with one digit (SCD80, SC79, SC75¹⁾) CES-Code

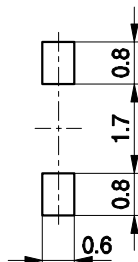
Month	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012	2013	2014
01	a	p	A	P	a	p	A	P	a	p	A	P
02	b	q	B	Q	b	q	B	Q	b	q	B	Q
03	c	r	C	R	c	r	C	R	c	r	C	R
04	d	s	D	S	d	s	D	S	d	s	D	S
05	e	t	E	T	e	t	E	T	e	t	E	T
06	f	u	F	U	f	u	F	U	f	u	F	U
07	g	v	G	V	g	v	G	V	g	v	G	V
08	h	x	H	X	h	x	H	X	h	x	H	X
09	j	y	J	Y	j	y	J	Y	j	y	J	Y
10	k	z	K	Z	k	z	K	Z	k	z	K	Z
11	l	2	L	4	l	2	L	4	l	2	L	4
12	n	3	N	5	n	3	N	5	n	3	N	5

1) New Marking Layout for SC75, implemented at October 2005.

Package Outline



Foot Print

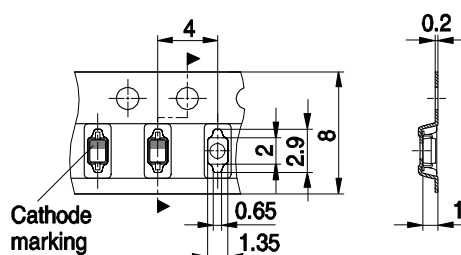


Marking Layout (Example)

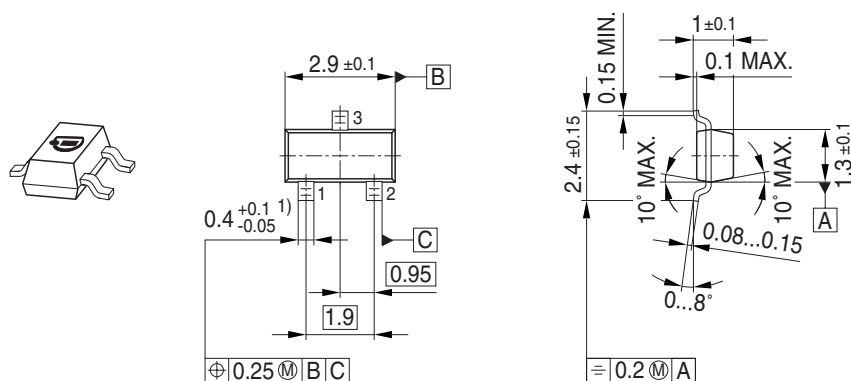


Standard Packing

Reel $\varnothing 180 \text{ mm}$ = 3.000 Pieces/Reel
 Reel $\varnothing 330 \text{ mm}$ = 10.000 Pieces/Reel

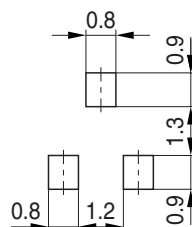


Package Outline

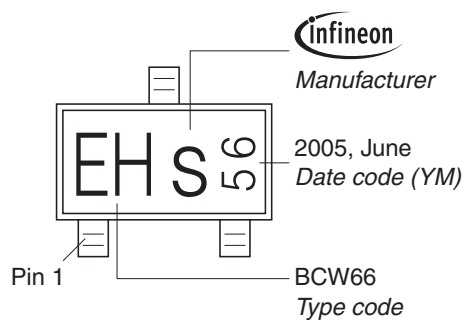


1) Lead width can be 0.6 max. in dambar area

Foot Print

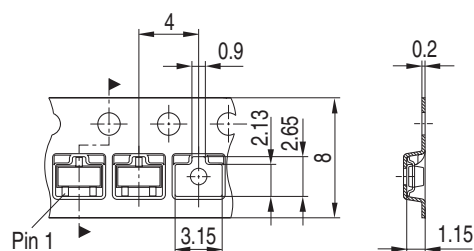


Marking Layout (Example)

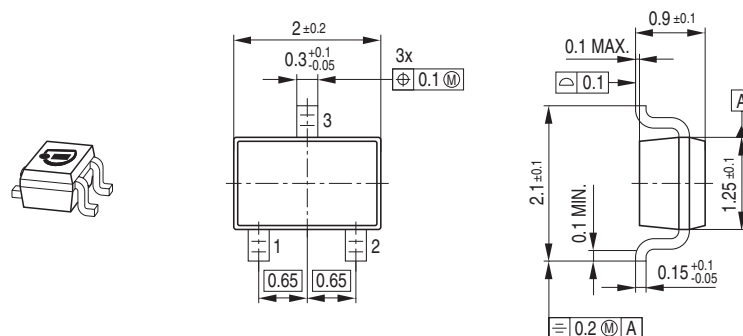


Standard Packing

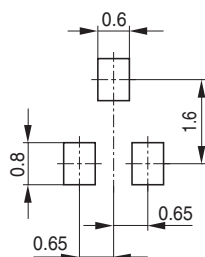
Reel ø180 mm = 3.000 Pieces/Reel
Reel ø330 mm = 10.000 Pieces/Reel



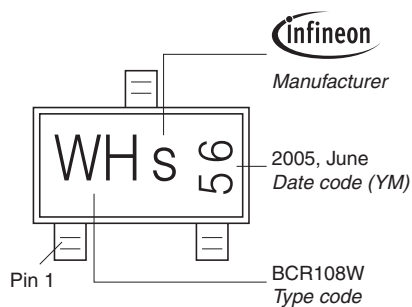
Package Outline



Foot Print

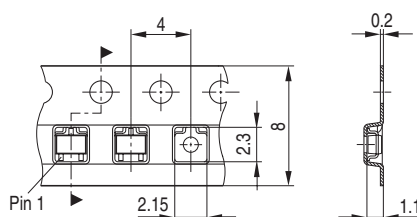


Marking Layout (Example)

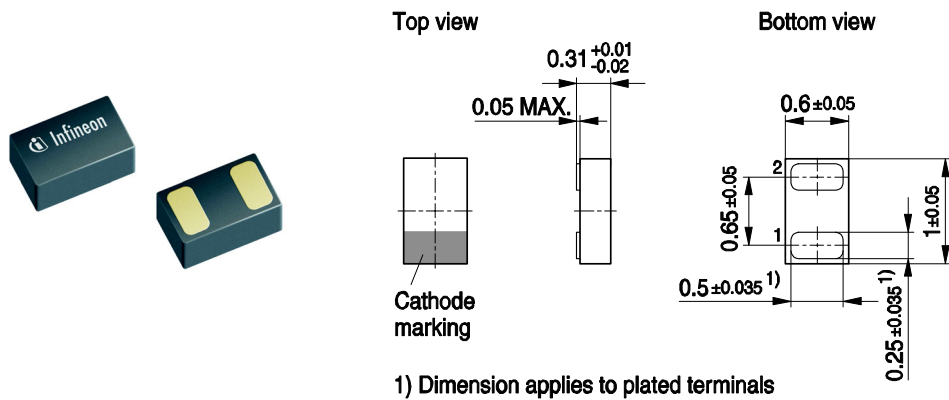


Standard Packing

Reel $\varnothing 180$ mm = 3.000 Pieces/Reel
 Reel $\varnothing 330$ mm = 10.000 Pieces/Reel



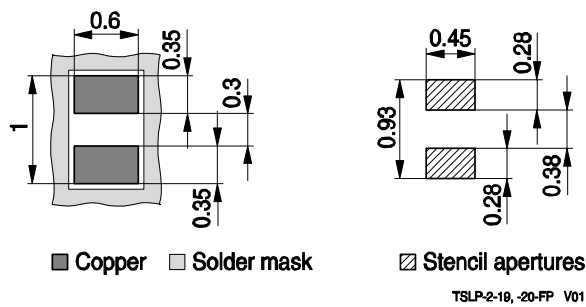
Package Outline



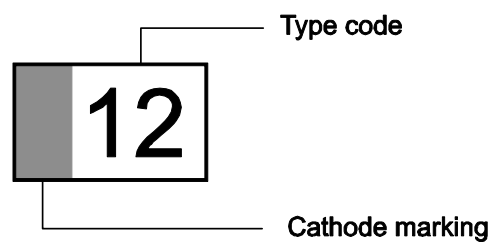
TSLP-2-19, -20-PO V01

Foot Print

For board assembly information please refer to Infineon website „Packages“

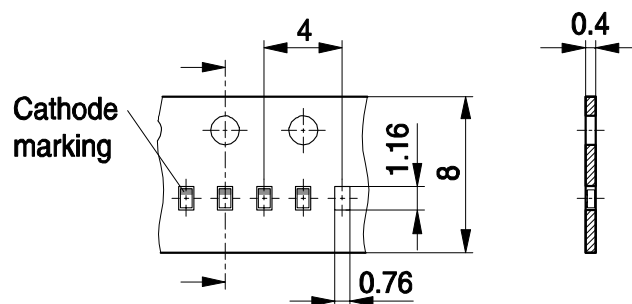


Marking layout (Example)



Standard Packing

Reel Ø 180 mm: 15.000 Pieces / Reel
 Reel Ø 330 mm: 6.000 Pieces / Reel
 Reel Ø 330 mm: 50.000 Pieces / Reel



TSLP-2-19, -20-TP V02

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